

Trench gate field-stop IGBT M series, 650 V, 15 A low-loss in a D²PAK package

Datasheet - production data

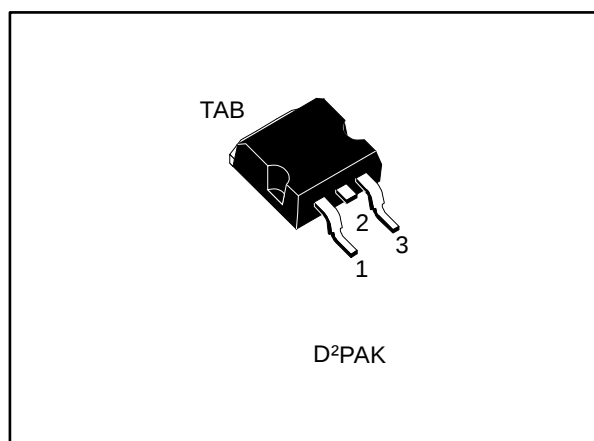
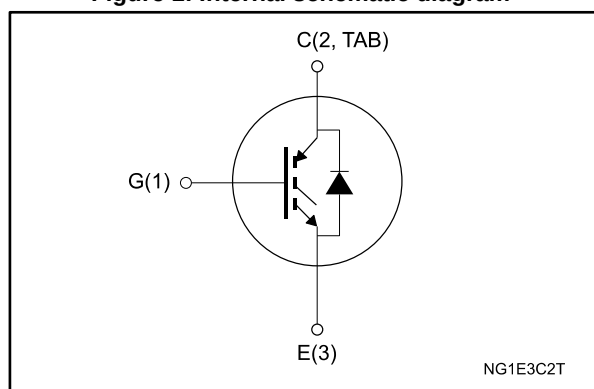


Figure 1: Internal schematic diagram



Features

- 6 μ s of short-circuit withstand time
- $V_{CE(sat)} = 1.55$ V (typ.) @ $I_C = 15$ A
- Tight parameter distribution
- Safer paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Soft and very fast recovery antiparallel diode
- Maximum junction temperature: $T_J = 175$ °C

Applications

- Motor control
- UPS
- PFC
- General purpose inverter

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the M series IGBTs, which represent an optimal balance between inverter system performance and efficiency where low-loss and short-circuit functionality are essential. Furthermore, the positive $V_{CE(sat)}$ temperature coefficient and tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGB15M65DF2	G15M65DF2	D ² PAK	Tape and reel

Contents

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$ V)	650	V
I_C	Continuous collector current at $T_C = 25$ °C	30	A
	Continuous collector current at $T_C = 100$ °C	15	
$I_{CP}^{(1)}$	Pulsed collector current	60	A
V_{GE}	Gate-emitter voltage	±20	V
I_F	Continuous forward current at $T_C = 25$ °C	30	A
	Continuous forward current at $T_C = 100$ °C	15	
$I_{FP}^{(1)}$	Pulsed forward current	60	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	136	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature range	- 55 to 175	°C

Notes:

⁽¹⁾Pulse width limited by maximum junction temperature.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case IGBT	1.1	°C/W
R_{thJC}	Thermal resistance junction-case diode	2.08	
R_{thJA}	Thermal resistance junction-ambient	62.5	

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4: Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 250\text{ }\mu\text{A}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$		1.55	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$, $T_J = 125\text{ °C}$		1.9		
		$V_{GE} = 15\text{ V}$, $I_C = 15\text{ A}$, $T_J = 175\text{ °C}$		2.1		
V_F	Forward on-voltage	$I_F = 15\text{ A}$		1.7	2.6	V
		$I_F = 15\text{ A}$, $T_J = 125\text{ °C}$		1.5		
		$I_F = 15\text{ A}$, $T_J = 175\text{ °C}$		1.4		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 500\text{ }\mu\text{A}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	μA

Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	1250	-	pF
C_{oes}	Output capacitance		-	80	-	
C_{res}	Reverse transfer capacitance		-	25	-	
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 30: "Gate charge test circuit")	-	45	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	
Q_{gc}	Gate-collector charge		-	15	-	

Table 6: IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 12\ \Omega$ (see Figure 29: "Test circuit for inductive load switching")		24	-	ns
t_r	Current rise time			7.8	-	ns
$(di/dt)_{on}$	Turn-on current slope			1570	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			93	-	ns
t_f	Current fall time			106	-	ns
$E_{on(1)}$	Turn-on switching energy			0.09	-	mJ
$E_{off(2)}$	Turn-off switching energy			0.45	-	mJ
E_{ts}	Total switching energy			0.54	-	mJ
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 15\text{ A}$, $V_{GE} = 15\text{ V}$, $R_G = 12\ \Omega$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")		24.8	-	ns
t_r	Current rise time			9.2	-	ns
$(di/dt)_{on}$	Turn-on current slope			1300	-	A/ μ s
$t_{d(off)}$	Turn-off-delay time			96	-	ns
t_f	Current fall time			169	-	ns
$E_{on(1)}$	Turn-on switching energy			0.22	-	mJ
$E_{off(2)}$	Turn-off switching energy			0.61	-	mJ
E_{ts}	Total switching energy			0.83	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 400\text{ V}$, $V_{GE} = 15\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	6		-	μ s
		$V_{CC} \leq 400\text{ V}$, $V_{GE} = 13\text{ V}$, $T_{Jstart} = 150\text{ }^\circ\text{C}$	10			

Notes:

(1)Including the reverse recovery of the diode.

(2)Including the tail of the collector current.

Table 7: Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 15\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$ (see Figure 29: "Test circuit for inductive load switching")	-	142	-	ns
Q_{rr}	Reverse recovery charge		-	525	-	nC
I_{rrm}	Reverse recovery current		-	13.4	-	A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	790	-	A/ μ s
E_{rr}	Reverse recovery energy		-	64	-	μ J
t_{rr}	Reverse recovery time	$I_F = 15\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 29: "Test circuit for inductive load switching")	-	241	-	ns
Q_{rr}	Reverse recovery charge		-	1690	-	nC
I_{rrm}	Reverse recovery current		-	20	-	A
dl_{rr}/dt	Peak rate of fall of reverse recovery current during t_b		-	420	-	A/ μ s
E_{rr}	Reverse recovery energy		-	176	-	μ J

2.1 Electrical characteristics (curves)

Figure 2: Power dissipation vs. case temperature

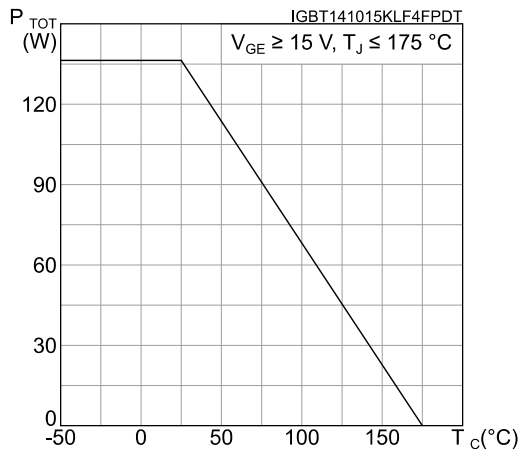


Figure 3: Collector current vs. case temperature

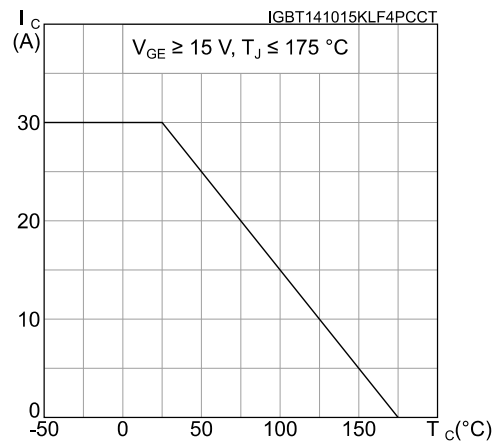
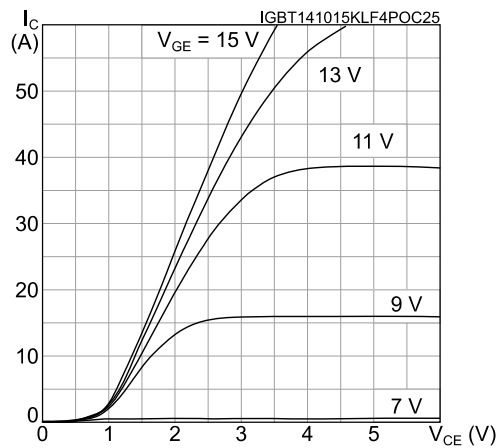
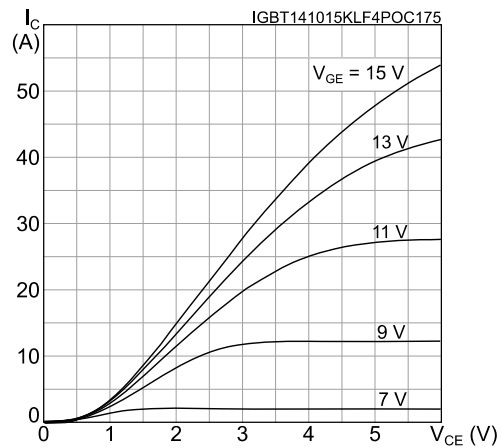
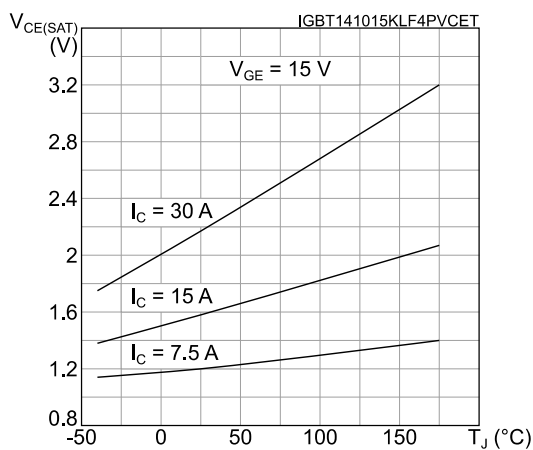
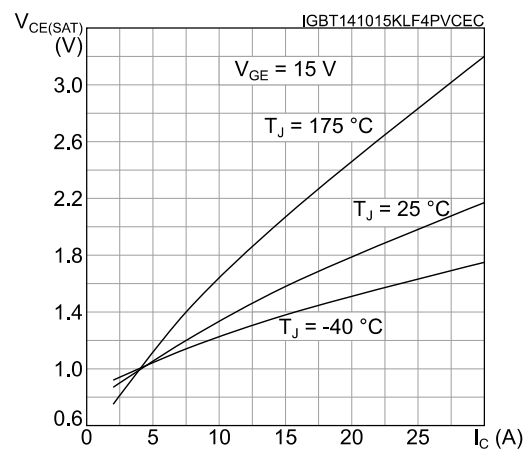
Figure 4: Output characteristics ($T_J = 25 \text{ }^{\circ}\text{C}$)Figure 5: Output characteristics ($T_J = 175 \text{ }^{\circ}\text{C}$)Figure 6: $V_{CE(sat)}$ vs. junction temperatureFigure 7: $V_{CE(sat)}$ vs. collector current

Figure 8: Collector current vs. switching frequency

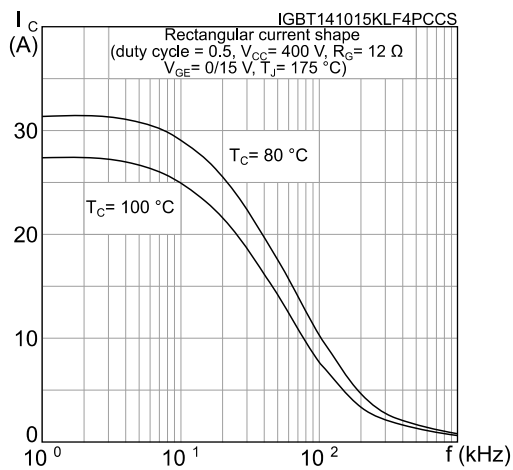


Figure 9: Forward bias safe operating area

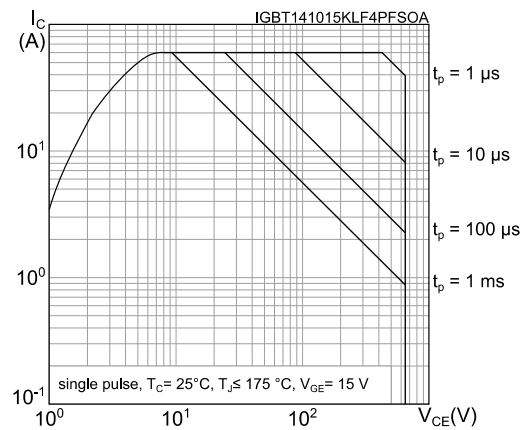


Figure 10: Transfer characteristics

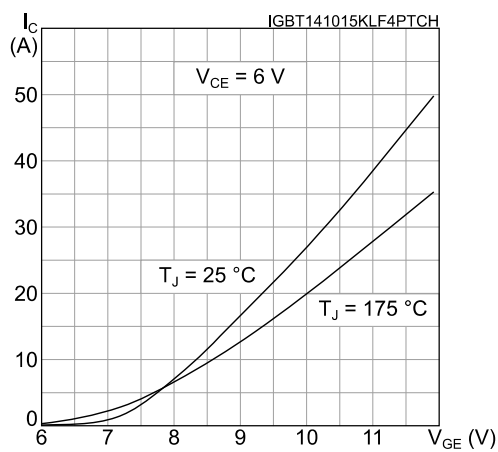
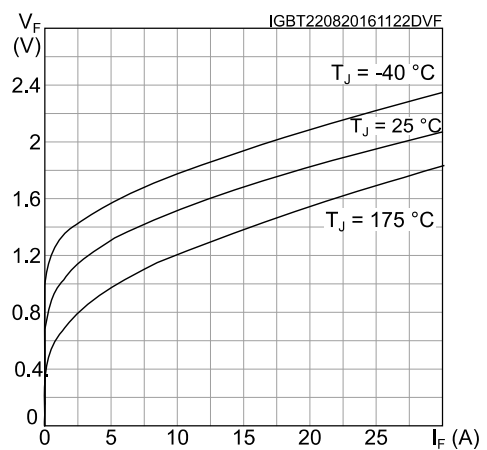
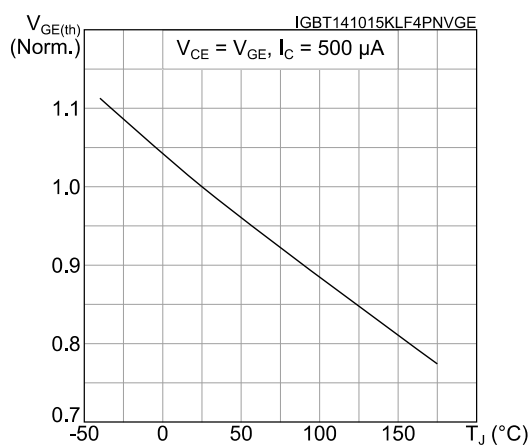
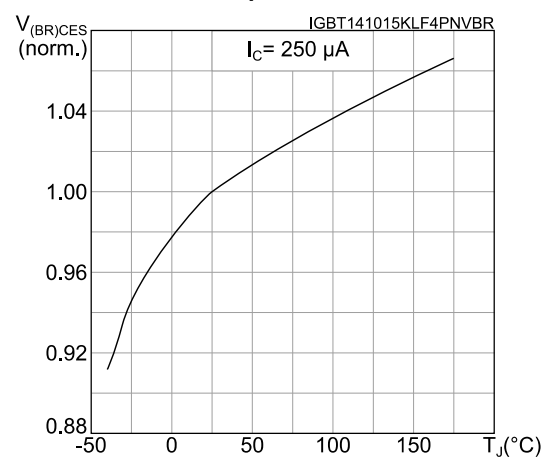
Figure 11: Diode V_F vs. forward currentFigure 12: Normalized $V_{GE(th)}$ vs. junction temperatureFigure 13: Normalized $V_{(BR)CES}$ vs. junction temperature

Figure 14: Capacitance variations

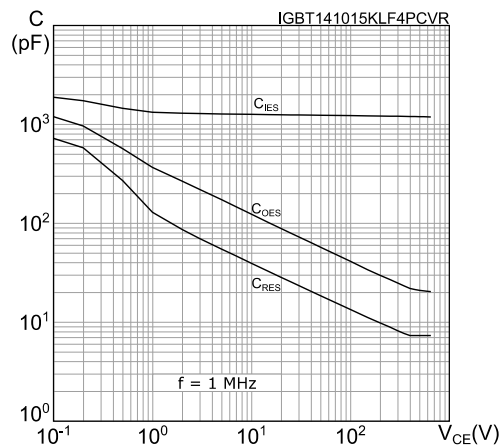


Figure 15: Gate charge vs. gate-emitter voltage

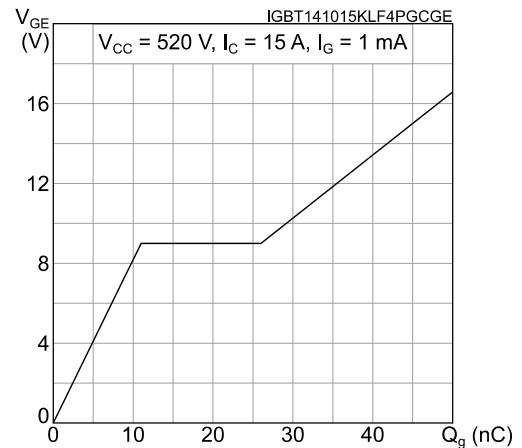


Figure 16: Switching energy vs. collector current

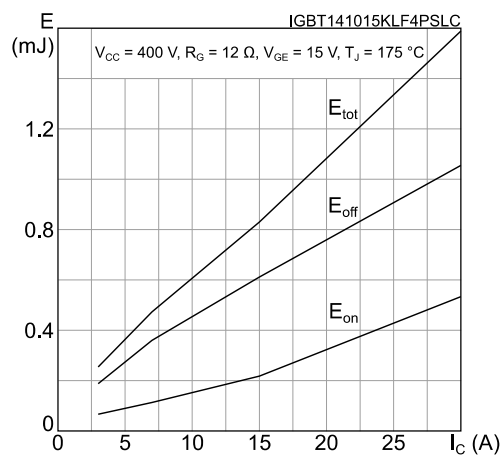


Figure 17: Switching energy vs. gate resistance

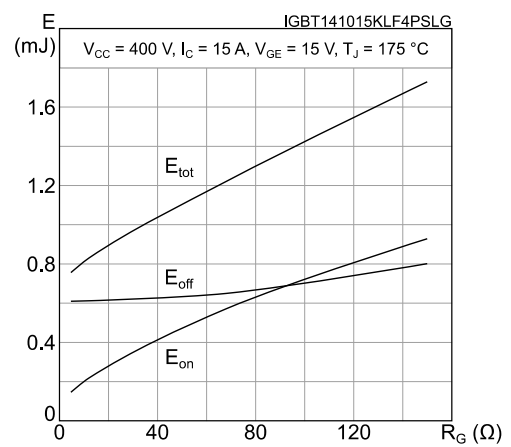


Figure 18: Switching energy vs. temperature

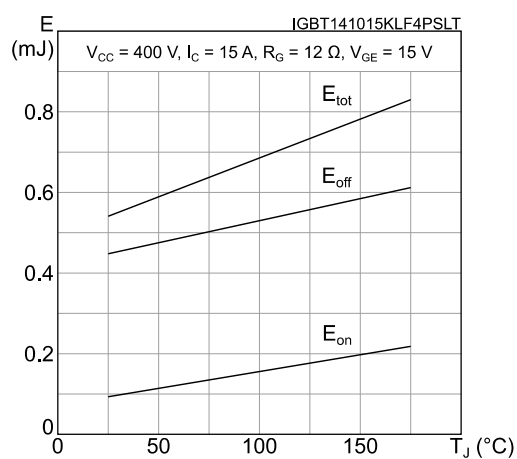


Figure 19: Switching energy vs. collector emitter voltage

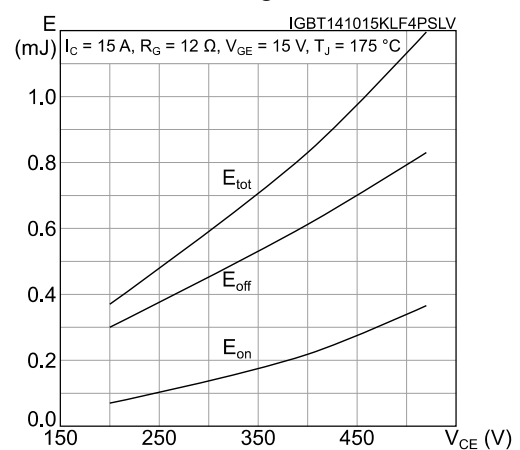


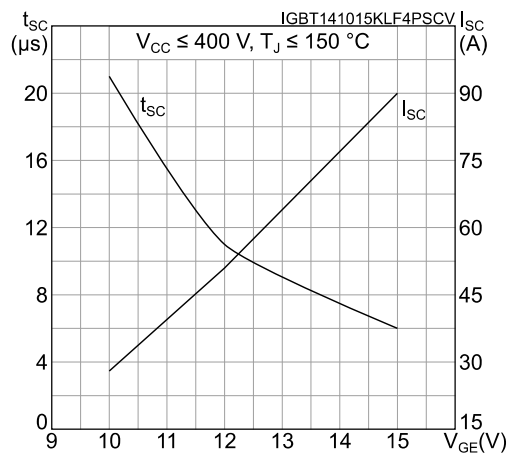
Figure 20: Short-circuit time and current vs. V_{GE} 

Figure 21: Switching times vs. collector current

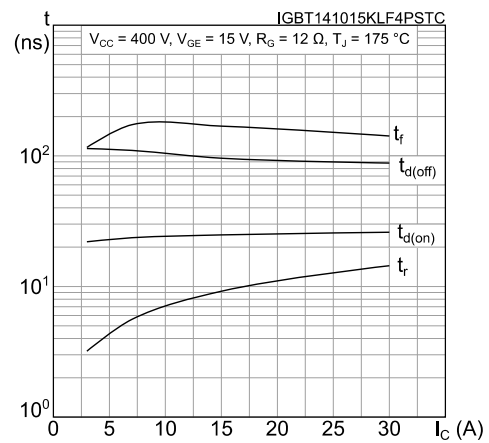


Figure 22: Switching times vs. gate resistance

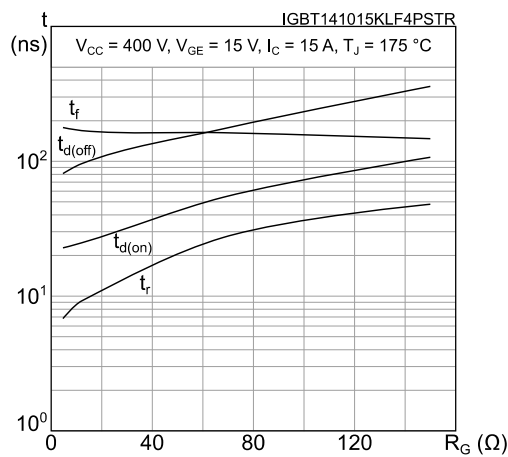


Figure 23: Reverse recovery current vs. diode current slope

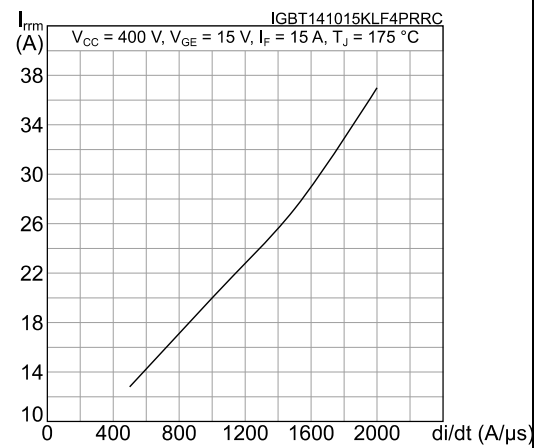


Figure 24: Reverse recovery time vs. diode current slope

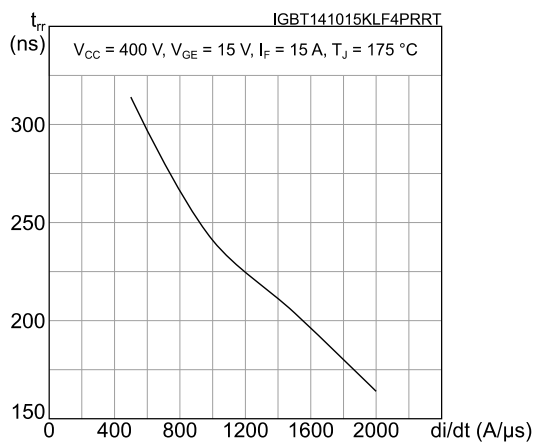


Figure 25: Reverse recovery charge vs. diode current slope

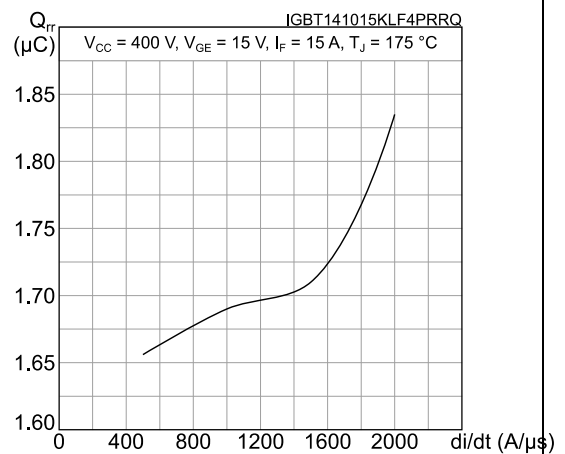


Figure 26: Reverse recovery energy vs. diode current slope

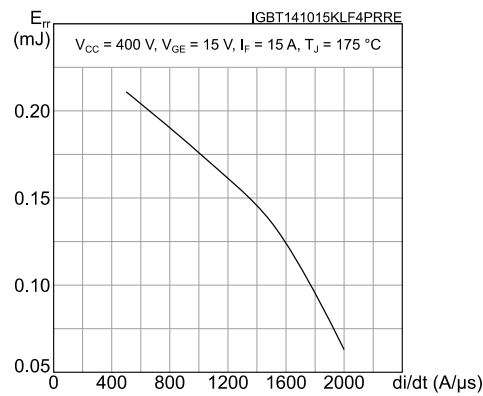


Figure 27: Thermal impedance for IGBT

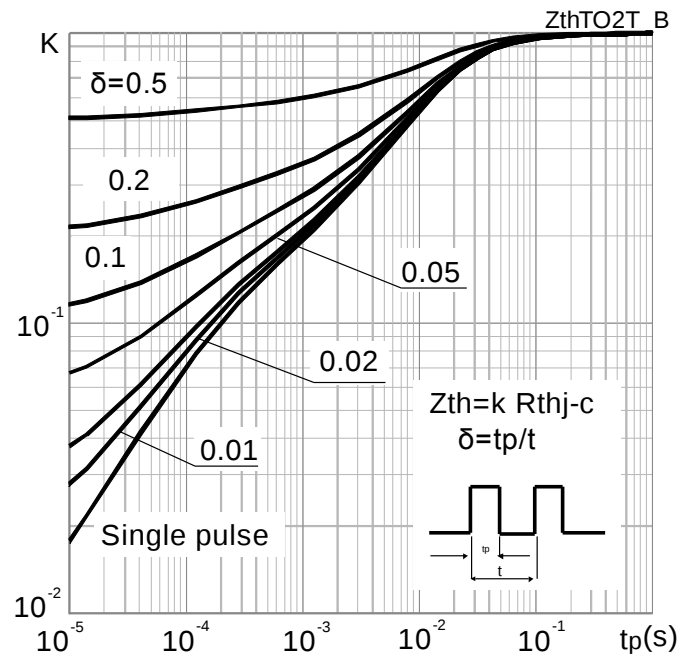
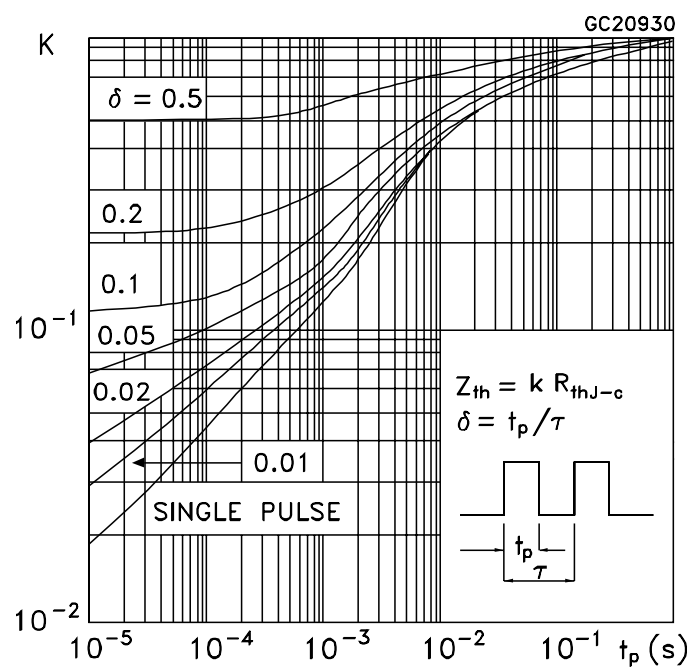
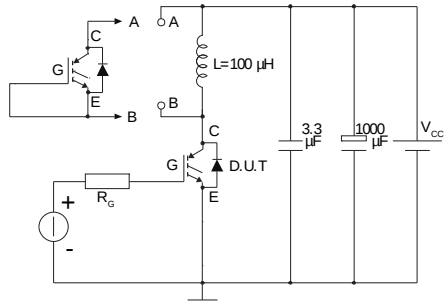


Figure 28: Thermal impedance for diode



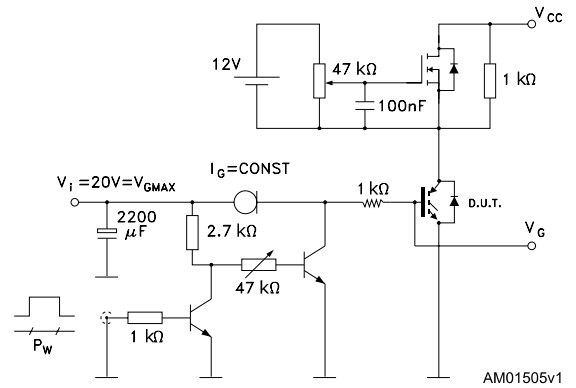
3 Test circuits

Figure 29: Test circuit for inductive load switching



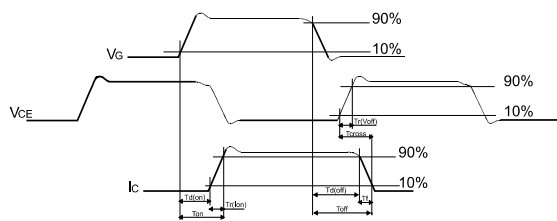
AM01504v1

Figure 30: Gate charge test circuit



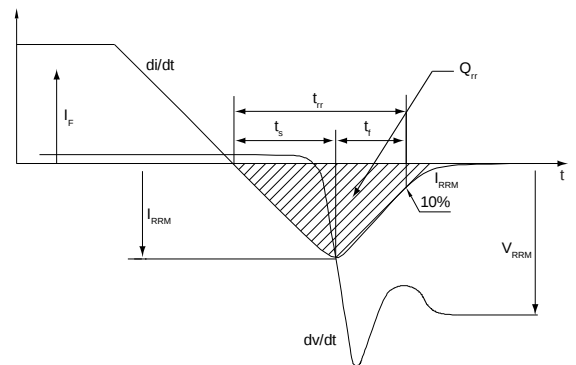
AM01505v1

Figure 31: Switching waveform



AM01506v1

Figure 32: Diode reverse recovery waveform



AM01507v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 33: D²PAK (TO-263) type A package outline

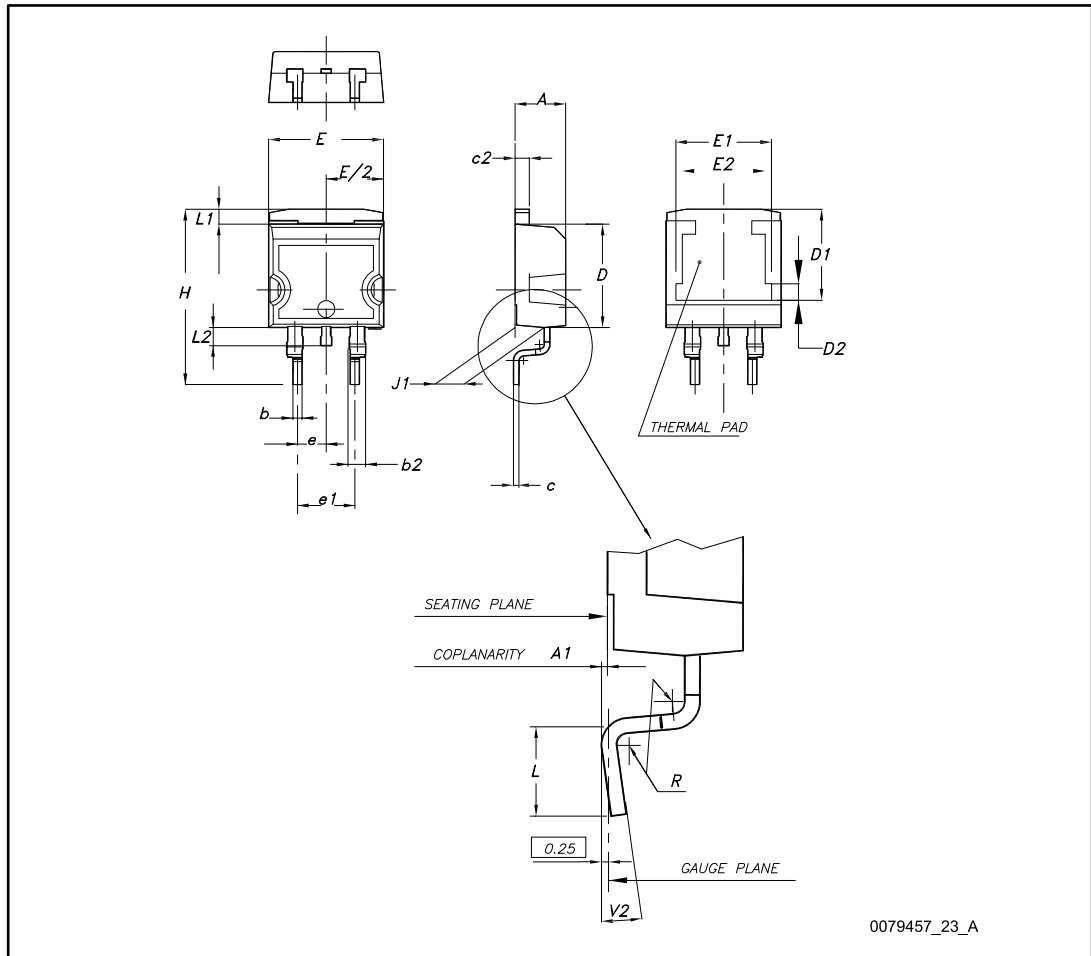
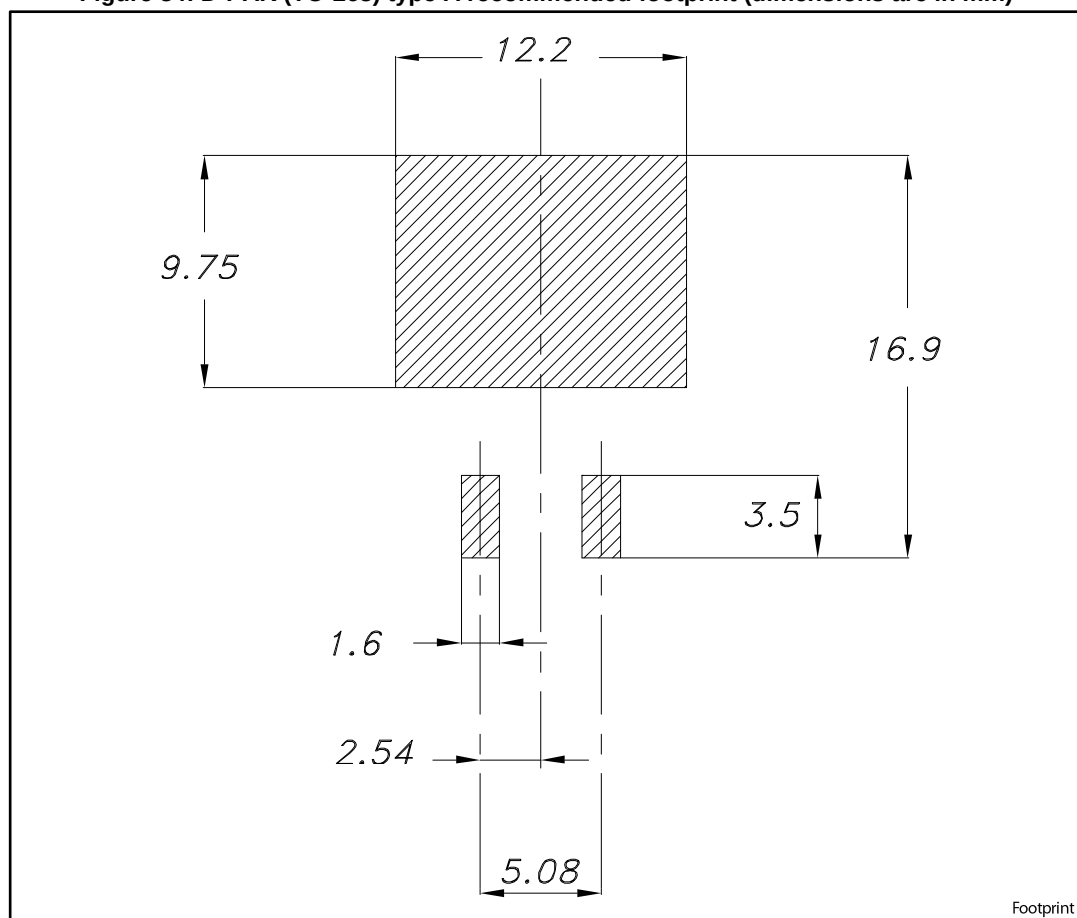


Table 8: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 34: D²PAK (TO-263) type A recommended footprint (dimensions are in mm)

4.2 D²PAK type A packing information

Figure 35: D²PAK type A tape outline

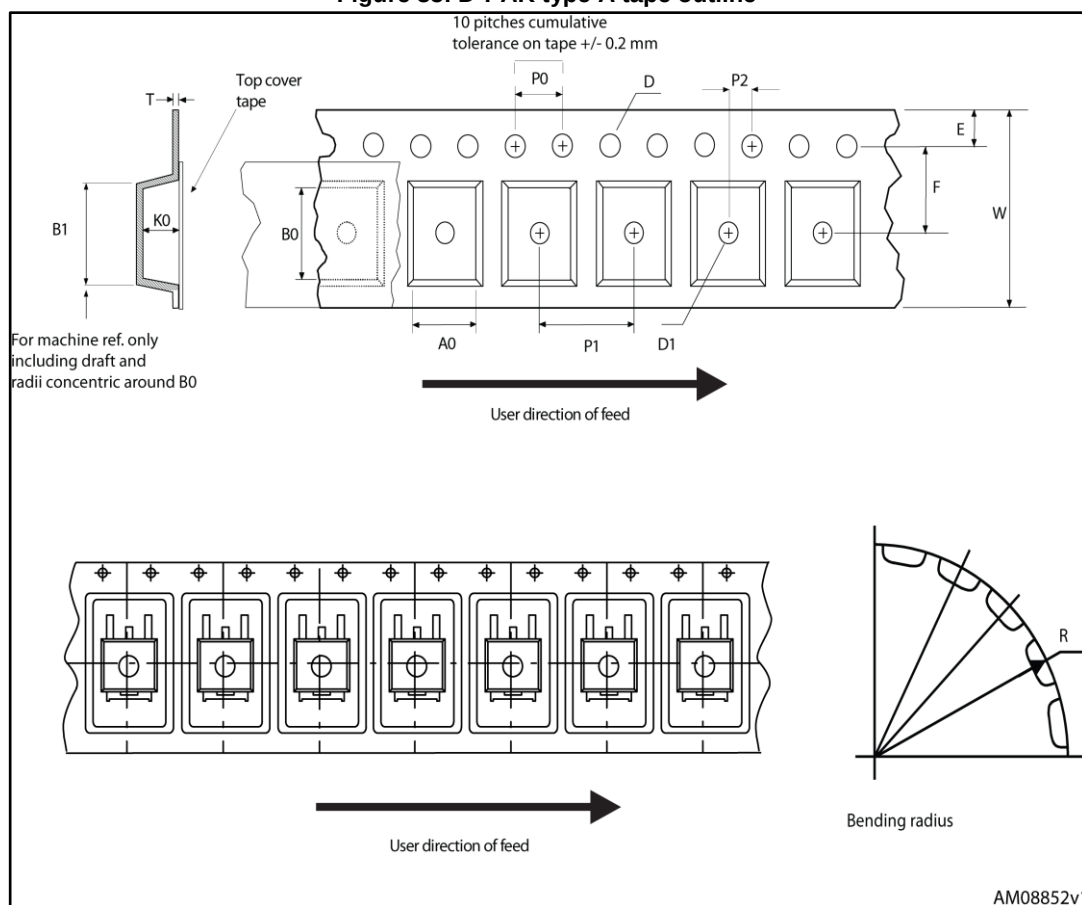
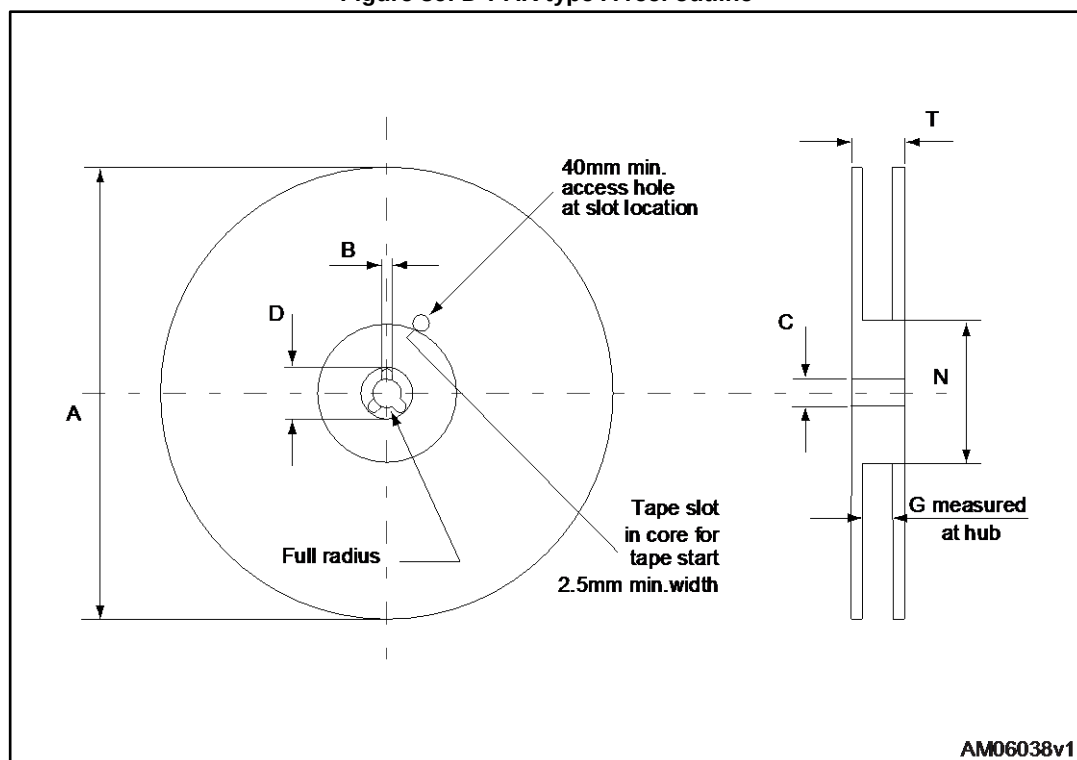


Figure 36: D²PAK type A reel outlineTable 9: D²PAK type A tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
14-Oct-2015	1	First release.
13-Nov-2015	2	Document status promoted from preliminary to production data.
22-Aug-2016	3	Updated <i>Table 2: "Absolute maximum ratings"</i> and <i>Table 6: "IGBT switching characteristics (inductive load)"</i> . Updated <i>Figure 16: "Switching energy vs. collector current"</i> , <i>Figure 17: "Switching energy vs. gate resistance"</i> , <i>Figure 18: "Switching energy vs. temperature"</i> and <i>Figure 19: "Switching energy vs. collector emitter voltage"</i> . Changed <i>Figure 11: "Diode VF vs. forward current"</i> .
04-May-2017	4	Modified: title, features and applications on cover page. Modified <i>Table 4: "Static characteristics"</i> , <i>Table 5: "Dynamic characteristics"</i> , <i>Table 7: "Diode switching characteristics (inductive load)"</i> . Updated <i>Section 4: "Package information"</i> . Minor text changes.

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